

1SS367

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

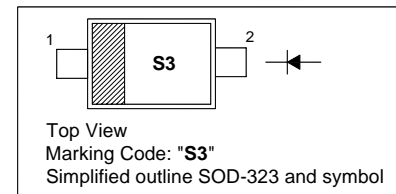
- Low forward voltage

Applications

- High Speed Switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

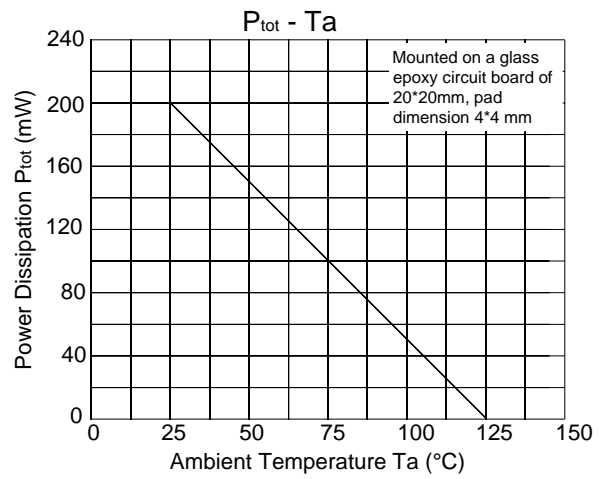
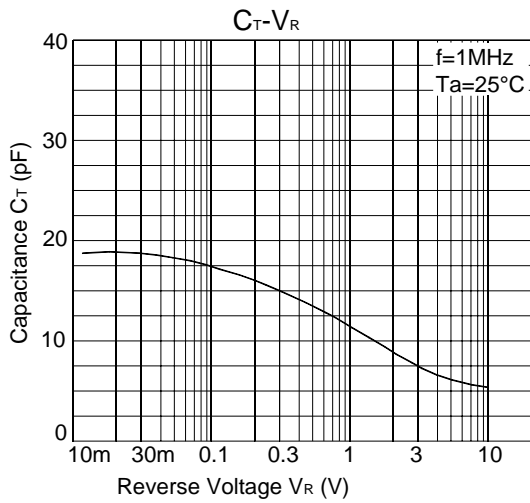
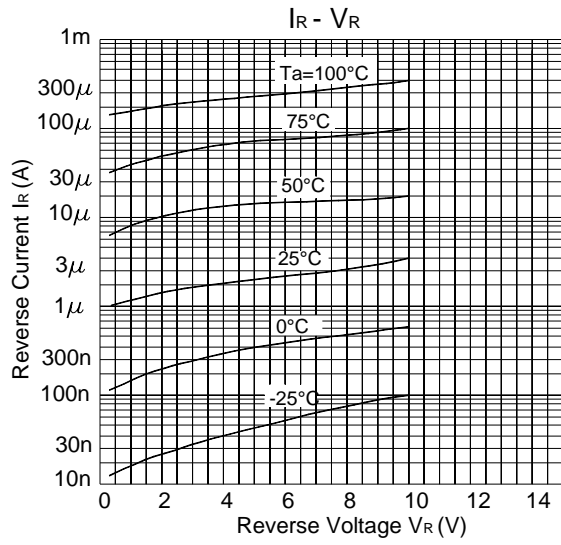
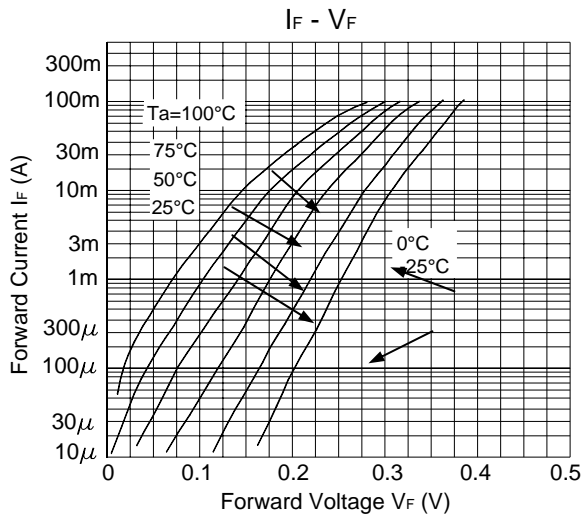


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	I_O	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Operating Temperature Range	T_{opr}	- 40 to + 100	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

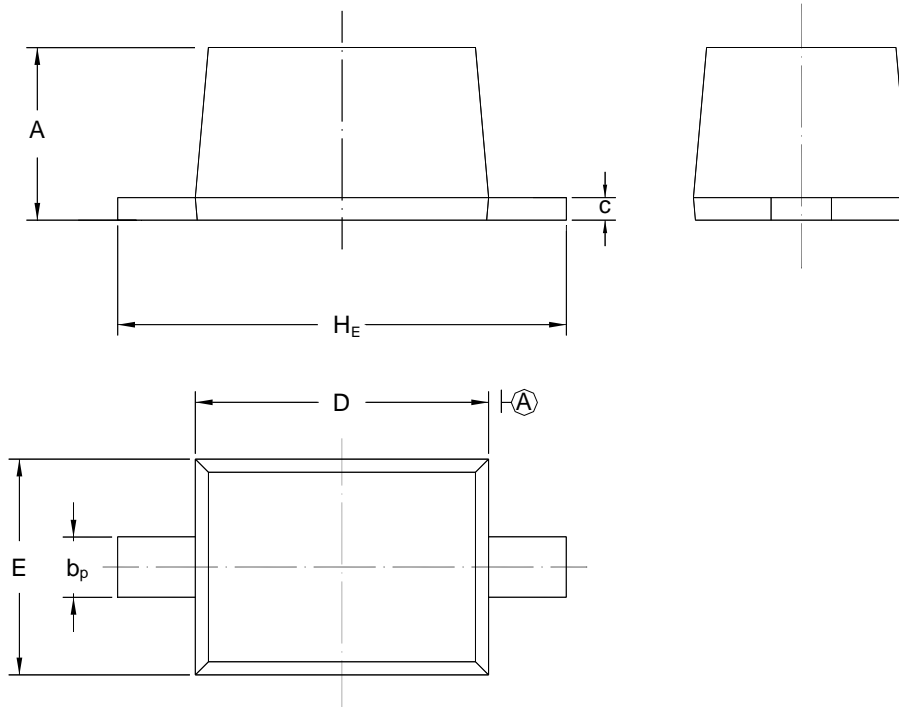
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.3 0.5	V
Reverse Current at $V_R = 10\text{ V}$	I_R	20	μA
Total Capacitance at $f = 1\text{ MHz}$	C_T	40	pF



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30